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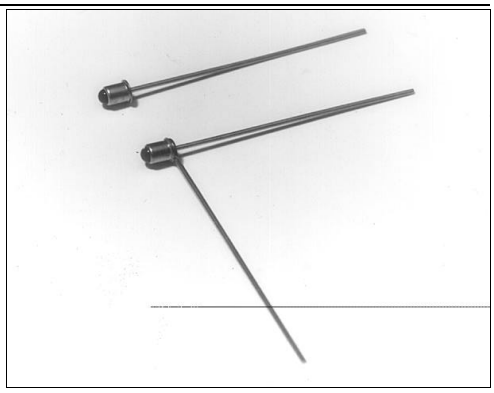
SE1470

AlGaAs Infrared Emitting Diode

FEATURES

- Compact metal can coaxial package
- 24° (nominal) beam angle
- 880 nm wavelength
- Higher output power than GaAs at equivalent drive currents
- Wide operating temperature range (- 55°C to +125°C)
- Mechanically and spectrally matched to SD1420 photodiode, SD1440 phototransistor and SD1410 photodarlington



INFRA-63.TIF

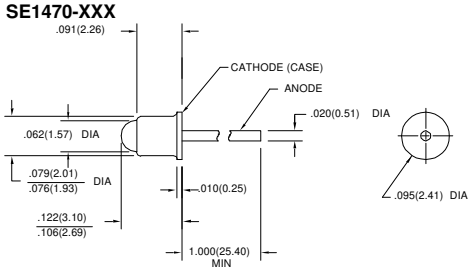
DESCRIPTION

The SE1470 is a high intensity aluminum gallium arsenide infrared emitting diode mounted in a glass lensed metal can coaxial package. The package may have a tab or second lead welded to the can as an optional feature (SE1470-XXXL). Both leads are flexible and may be formed as required to fit various mounting configurations. These devices typically exhibit 70% greater power intensity than gallium arsenide devices at the same forward current.

OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals	±0.005(0.12)
	2 plc decimals	±0.020(0.51)

SE1470-XXX



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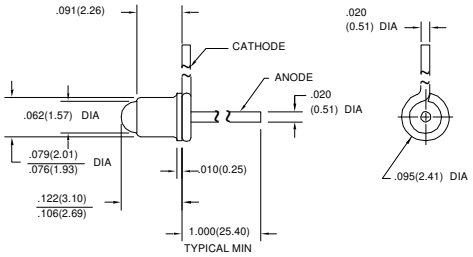
SE1470-XXXL



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Honeywell

SE1470

AlGaAs Infrared Emitting Diode

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Irradiance [1]	H				mW/cm²	I_F=20 mA
SE1470-001, SE1470-001 L		0.35				
SE1470-002, SE1470-002 L		0.65				
SE1470-003, SE1470-003 L		1.10		4.5		
SE1470-004, SE1470-004 L		1.65				
Forward Voltage	V_F			1.8	V	I_F=50 mA
Reverse Breakdown Voltage	V_{BR}	3.0			V	I_R=10 µA
Peak Output Wavelength	λ_p		880		nm	
Spectral Bandwidth	$\Delta\lambda$		80		nm	
Spectral Shift With Temperature	$\Delta\lambda_p/\Delta_T$		0.2		nm/°C	
Beam Angle [2]	Ø		24		degr.	I_F=Constant
Radiation Rise And Fall Time	t_r, t_f		0.7		µs	

Notes
1. Measured in mW/cm² into a 0.104 (2.64) diameter aperture placed 0.535(13.6) from the lens tip.
2. Beam angle is defined as the total included angle between the half intensity points.

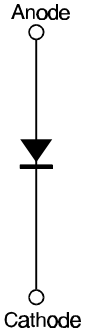
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Continuous Forward Current	50 mA
Power Dissipation	75 mW [1]
Operating Temperature Range	-55°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (10 sec)	260°C

Notes
1. Derate linearly from 25°C free-air temperature at the rate of 0.71 mW/°C.

SCHEMATIC



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SE1470

AlGaAs Infrared Emitting Diode

Fig. 1 Radiant Intensity vs Angular Displacement

gra_007.ds4

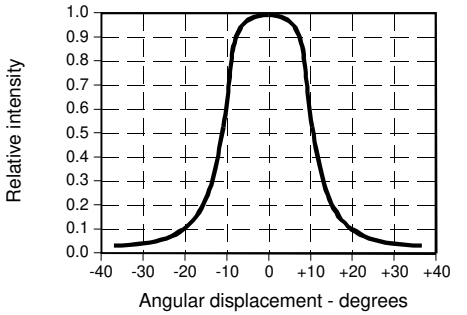

Fig. 2 Radiant Intensity vs Forward Current

gra_008.ds4

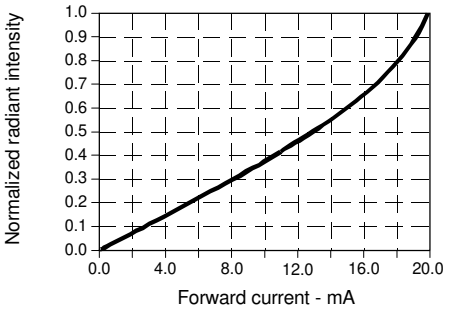

Fig. 3 Forward Voltage vs Forward Current

gra_201.ds4

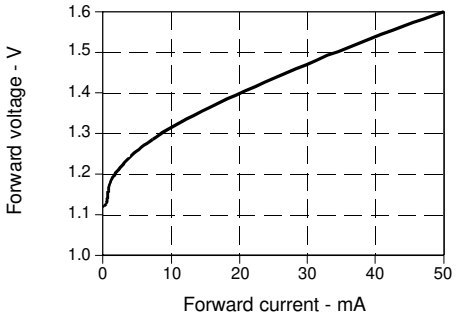

Fig. 4 Forward Voltage vs Temperature

gra_202.ds4

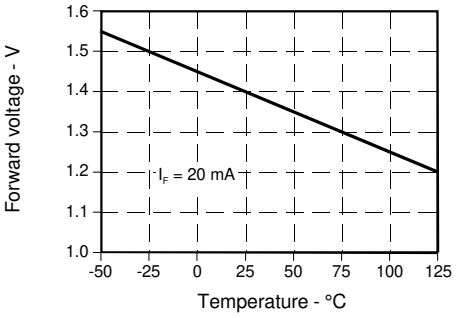

Fig. 5 Spectral Bandwidth

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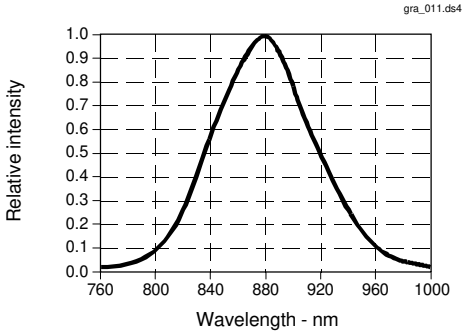
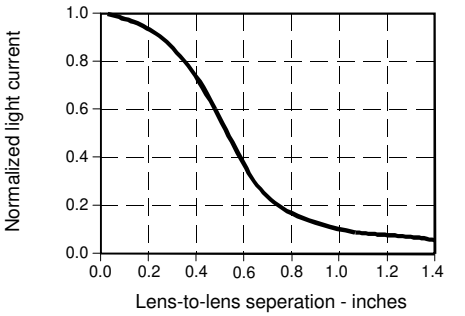


Fig. 6 Coupling Characteristics with SD1440

gra_012.ds4



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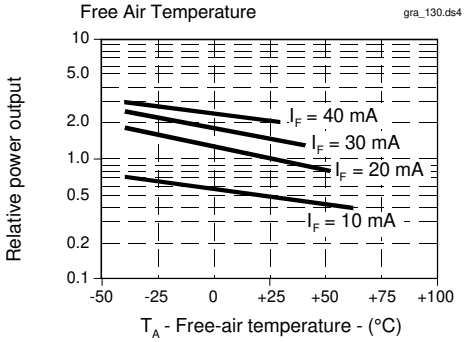
AlGaAs Infrared Emitting Diode

Fig. 7 Relative Power Output vs Free Air Temperature



All Performance Curves Show Typical Values